

## EAST Search History

## EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	16	"10574186" "10599127" "60042411" "60731783" "11850668" "60824465" "29155461" "11464590" "11465303" "11557151" "11610432" "12239694" "60749997" "60862803" "60946251" "60985328" "61094297" "10574186"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/16 09:37
S2	4533	(29/592,1,599,601).OCLS	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/04/16 12:32
S3	1153	S2 and alumin\$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/16 12:55
S4	468	"1745175" "1900018" "439457" "2524035" "2569347"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/16 13:03

S5	1035955	transistor	US; PCPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/16 13:13
S6	1815417	S2 and transistor or gate or drain	US; PCPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/16 13:36
S7	319	S2 and (transistor or gate or drain)	US; PCPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/16 13:37
S8	1344516	pore hole aperture	USPAT	OR	ON	2009/04/16 14:41
S9	1850187	active carbon superconductor semiconductor magnet\$2 smart	USPAT	OR	ON	2009/04/16 14:41
S10	131421	anodiz\$3 anodization electrolyt\$4	USPAT	OR	ON	2009/04/16 14:43
S11	723762	alumin\$4	USPAT	OR	ON	2009/04/16 14:44
S12	1781315	transistor source drain gate	USPAT	OR	ON	2009/04/16 14:44
S13	444341	S9 same S12	USPAT	OR	ON	2009/04/16 14:46
S14	18630	S8 same S10	USPAT	OR	ON	2009/04/16 14:47

S15	3913	S14 and S13	USPAT	OR	ON	2009/04/16 14:47
S16	2699	S11 and S15	USPAT	OR	ON	2009/04/16 14:48
S17	313	transistor and pore and anodiz\$4	USPAT	OR	ON	2009/04/16 14:58
S18	199	(977/890).CCL.S	US-PGPUB; USPAT; USOCR; FPRS; EPC; JPO; DERWENT; IBM_TDB	OR	OFF	2009/04/20 09:53
S20	173	2006/0046602 11/167,067 10/747,438 9/178,680 11/162,548 "6325909" 11/466,217 10/301,715 11/119,531 10/033,032 10/336,236	US-PGPUB; USPAT; USOCR; FPRS; EPC; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/20 11:30
S21	40	(10/033032   10/301715   10/336236   10/394435   10/747438   10/824678   10/824679   10/824706   10/829660   10/863972   10/864045   10/864186   10/864572   10/864681   10/864682   10/864751   10/887860   10/917606   10/917794   10/917893   10/917932   10/918085   10/918181   10/935994   10/936119   10/967858   10/018370   11/032823   11/032983   11/033087   11/033089   11/033213   11/033215   11/033216   11/048231   11/053135   11/119531   11/162548   11/167067   11/188678   11/197196   11/213830   11/227468   11/280786   11/338512   11/338513   11/449969   11/466893   11/497797   11/527127   11/541834	USPAT; USOCR	OR	ON	2009/04/20 11:32

		11/542524   11/602795   11/643688   11/651177   11/653673   11/656253   11/731946   11/742290   11/835583   11/835612   11/835613   11/835651   11/835759   11/835845   11/835852   11/835856   11/835865   11/860929   11/870872   11/870897   11/892251   11/928538   11/928651   11/929076   11/945710   11/971476   12/023867   12/029118   12/029661   12/046855   12/114540   12/195675   12/202737   12/246009).APP.				
S22	133	S20 not S21	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/20 11:33
S23	47	S22 and pore	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/20 11:41
S24	18	((AAO or alumina or (anodi\$4 same aluminum)) with ((carbon and (nano\$1tube or nanotube)) and (transistor or FET)))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/20 13:06
S25	0	("2007/0001220").URPN.	USPAT	OR	ON	2009/04/20 13:49

S26	19	"20020130311" "20060292870" "6740910"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/21 09:32
S27	13447	((427/245,247,458,469,126.3) or (205/75,149,150,112) or (29/846,896.6,825,830,831,850)).OCLS.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	OFF	2009/10/29 14:19
S28	1346	((427/245) or (205/112) or (29/896.6)).OCLS.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	OFF	2009/10/29 14:20
S29	70	S28 and (anodized anodizing anodization electrolytic electrolyte) same (pore hole aperture micropor\$4 foraminous)	US-PGPUB; USPAT; FPRS; EPO	OR	ON	2009/10/29 15:19
S30	382204	"257".clas. "438".clas. "977".clas.	US-PGPUB; USPAT; FPRS; EPO	OR	ON	2009/10/29 15:36
S31	5191	S30 and (anodized anodizing anodization electrolytic electrolyte) same (pore hole aperture micropor\$4 foraminous)	US-PGPUB; USPAT; FPRS; EPO	OR	ON	2009/10/29 15:37
S32	2	"20060011972"	US-PGPUB; USPAT; FPRS; EPO	OR	ON	2009/10/29 15:37
S33	2280	S30 and (anodized anodizing anodization electrolytic electrolyte) same (pore hole aperture micropor\$4 foraminous) and (transistor gate drain)	US-PGPUB; USPAT; FPRS; EPO	OR	ON	2009/10/29 15:38

S34	1980	S30 and (anodized anodizing anodization electrolytic electrolyte) same (pore hole aperture micropor\$4 foraminous) and (transistor gate drain) and insulat\$4 and (semiconductor superconductor magnetic carbon)	US-PGPUB; USPAT; FPRS; EPO	OR	ON	2009/10/29 15:39
S35	1	"20030132461"	US-PGPUB; USPAT; FPRS; EPO	OR	ON	2009/10/29 15:40
S36	1497	S30 and (anodized anodizing anodization electrolytic electrolyte) same (pore hole aperture micropor\$4 foraminous) and (transistor gate drain) and insulat\$4 and (semiconductor superconductor magnetic carbon) and alumin\$4	US-PGPUB; USPAT; FPRS; EPO	OR	ON	2009/10/29 15:49
S37	6	("4501663"   "4687551"   "5112449").PN. OR ("5259957").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/10/29 15:50
S38	58	S28 and (anodized anodizing anodization electrolytic electrolyte) same (pore hole aperture micropor\$4 foraminous) same (form\$4 creat\$4)	US-PGPUB; USPAT; FPRS; EPO	OR	ON	2009/10/29 16:09
S39	19	S28 and (anodized anodizing anodization electrolytic electrolyte) same (pore hole aperture micropor\$4 foraminous) same (second direction)	US-PGPUB; USPAT; FPRS; EPO	OR	ON	2009/10/29 16:17
S40	13	("3850762").PN. OR ("4687551").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/10/29 16:33
S41	6	("4501663"   "4687551"   "5112449").PN. OR ("5259957").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/10/29 16:36
S42	4	((("5508209") or ("5576231"))).PN.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	OFF	2009/10/30 17:43

S43	0	S42 and (anodized anodizing anodization electrolytic electrolyte) same (pore hole aperture micropor\$4 foraminous) and (transistor gate drain) and insulat\$4 and (semiconductor superconductor magnetic carbon) and alumin\$4	US-PGPUB; USPAT; FPRS; EPO	OR	ON	2009/10/30 17:46
S44	12	("20020130311"   "20020130311"   "20040149979"   "4687551"   "5259957"   "6325909"   "6325909"   "6740910").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/02/20 16:02

### EAST Search History (Interference)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S45	0	(electronic support material anodizing direction surface pore).clm.	USPAT; UPAD	AND	ON	2010/02/20 16:14

2/ 20/ 2010 4:59:07 PM

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